

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (canceled)
2. (canceled)
3. (canceled)
4. (canceled)
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)
9. (canceled)
10. (canceled)

11. (currently amended) A semiconductor integrated circuit device comprising:
trenches formed in a semiconductor substrate and defining active regions and dummy regions; and
element isolation insulating films buried in said trenches by polishing an insulating layer formed over said trenches and said semiconductor substrate such that said element isolation insulating films serve as element isolation regions,
wherein said dummy regions are formed at a scribing area.

12. (previously presented) A semiconductor integrated circuit device according to claim 11, wherein a length of said dummy region is shorter than a distance between external terminals.

13. (currently amended) A semiconductor integrated circuit device comprising:
trenches formed in a semiconductor substrate and defining active regions and dummy regions; and

insulating films buried in said trenches by polishing an insulating layer formed over said trenches and said semiconductor substrate such that said insulating films serve as element isolation insulating films;

wherein said dummy regions are formed at a scribing area.

14. (previously presented) A semiconductor integrated circuit device according to claim 13, wherein a length of said dummy region is shorter than a distance between bonding pads.

15. (currently amended) A semiconductor integrated circuit device comprising:
trenches formed in a semiconductor substrate and defining active regions and dummy regions; and

element isolation insulating films buried in said trenches by polishing an insulating layer formed over said trenches and said semiconductor substrate,

wherein said dummy regions are formed at a scribing area.

16. (previously presented) A semiconductor integrated circuit device according to claim 15, wherein a length of said dummy region is shorter than a distance between external terminals.